

Amendments to the Claims:

1. (Previously Presented) An electronic device comprising a substrate and an electronic circuit element flip-chip-connected on said substrate,

wherein a connection is made by gold-tin (Au-Sn) bonding between a chip electrode of said electronic circuit element and an internal electrode on said substrate, and

the connection is sealed between said electronic circuit element and said substrate opposed to said electronic circuit element in a peripheral connection also formed therebetween by the gold-tin bonding, and

an alloy containing gold and tin is formed in each of the connection and the peripheral connection.

2. (Original) The electronic device according to claim 1,

wherein said electronic circuit element comprises a piezoelectric element.

3. (Original) The electronic device according to claim 1,

wherein said electronic circuit element comprises a SAW chip, a thin film bulk acoustic resonator (FBAR) or a microelectromechanical system (MEMS).

4. (Previously Presented) The electronic device according to claim 1,

wherein said the surface of the electrode on said electronic circuit element is plated with gold (Au) and the surface of the internal electrode on said substrate is plated with tin (Sn).

5. (Original) The electronic device according to claim 1,

wherein said substrate comprises a printed substrate or a flexible substrate.

6. (Original) The electronic device according to claim 1,

wherein said substrate comprises a metal core substrate.

7. (Original) The electronic device according to claim 1,

wherein said substrate comprises a glass substrate or a ceramic

substrate.

8. (Original) The electronic device according to claim 1,
wherein said substrate comprises a silicon substrate.

9. (Previously Presented) The electronic device according to claim 6,
wherein the metal core substrate has a core metal and a resin layer
attached to a surface of the core metal opposite to the electronic circuit element,
a portion of the surface the core metal exposed from the resin layer is
metalized to form the peripheral connection formed thereon, and the peripheral
connection and the core metal are electrically connected to each other.

10. (Canceled).

11. (Canceled).

12. (Canceled).

13. (Canceled).

14. (Canceled).

15. (Canceled).

16. (Canceled).

17. (Canceled).

18. (Canceled).

19. (Previously Presented) The electronic device according to claim 1,
wherein the alloy containing gold and tin is a gold-tin intermetallic
compound.

20. (Previously Presented) The electronic device according to claim 19,
wherein a melting point of the gold-tin intermetallic compound is higher
than that of tin.

21. (Previously Presented) The electronic device according to claim 19,
wherein the chip electrode and a first metal layer surrounding the chip
electrode are formed on a surface of the electronic circuit element opposite to a
surface of the substrate,

the internal electrode and a second metal layer surrounding the internal

electrode are formed on the surface of the substrate opposite to the surface of the electronic circuit element, and

the peripheral connection including the alloy containing gold and tin is formed between the first metal layer and the second metal layer.

22. (Previously Presented) The electronic device according to claim 21, wherein a gold bump is formed on the chip electrode, a gold projection is formed on the first metal layer, a tin layer is formed on each of a surface of the internal electrode and a surface of the second metal layer both opposite to the surface of the electronic circuit element,

the alloy containing gold and tin is formed in the connection at an interface between the tin layer on the internal electrode and the gold bump contacting with each other, and

the alloy containing gold and tin is formed in the peripheral connection at an interface between the tin layer on the second metal layer and the gold projection contacting with each other.

23. (Previously Presented) The electronic device according to claim 22, wherein each of the alloys containing gold and tin formed in the connection and the peripheral connection is the gold-tin intermetallic compound having a melting point higher than that of tin.

24. (Previously Presented) The electronic device according to claim 22, wherein each of the tin layers on the internal electrode and the second metal layer consists only of tin.

25. (Previously Presented) The electronic device according to claim 22, wherein the tin layer is formed by plating each of the internal electrode and the second metal layer with tin.

26. (Previously Presented) The electronic device according to claim 22, wherein the chip electrode and the first metal layer are formed of aluminum.

27. (Previously Presented) The electronic device according to claim 22, wherein the internal electrode and the second metal layer are formed of copper.

28. (Previously Presented) The electronic device according to claim 1, wherein the alloy containing gold and tin is formed by melting the tin layers at the respective interfaces between the tin layer on the internal electrode and the gold bump and between the tin layer on the second metal layer and the gold projection.

29. (Previously Presented) The electronic device according to claim 1, wherein the connection is encapsulated in an airtight manner between the electronic circuit element and the substrate opposed to each other by the peripheral connection.

30. (Previously Presented) An electronic device comprising:
an electronic circuit element having a first surface on which a first electrode is formed; and
a substrate having a second surface arranged opposite to the first surface, and a second electrode electrically being formed on the second surface and connected to the first electrode,

wherein a sealing member is formed between the first surface of the electronic circuit element and the second surface of the substrate to surround the first electrode in the first surface and the second electrode in the second surface,

the sealing member has an alloy including tin (Sn) and gold (Au) being formed therein and having a melting point higher than the melting point of tin.

31. (Previously Presented) The electronic device according to claim 30, wherein the alloy including tin and gold is a gold-tin intermetallic compound.